

This listing of claims will replace all prior versions of claims in the application.

Claims 1-40. (cancelled).

Claim 41. (new) A chemically-amplified positive tone photoresist, the photoresist comprising a resin, a photoacid-generating compound and an amine other than a trialkylamine.

Claim 42. (new) The photoresist of claim 41 wherein the amine is an aryl amine.

Claim 43. (new) The photoresist of claim 41 wherein the amine is a cyclic amine.

Claim 44. (new) The photoresist of claim 41 wherein the photoacid-generating compound is an iodonium compound.

Claim 45. (new) The photoresist of claim 41 wherein the photoacid-generating compound is an aromatic sulfonium salt.

Claim 46. (new) The photoresist of claim 41 wherein the resin is a phenol-based polymer.

Claim 47. (new) An article of manufacture comprising a wafer substrate having coated thereon a photoresist of claim 41.

Claim 48. (new) A method for forming a photoresist image on a wafer substrate for the production of a microprocessor, comprising:

(a) providing a chemically amplified positive tone photoresist, the photoresist comprising i) a resin, ii) a photoacid-generating compound and iii) a compound that comprises one or more moieties selected from ether, ester and amide.

Claim 49. (new) The method of claim 48 wherein the compound iii) comprises one or more ether moieties.

Claim 50. (new) The method of claim 48 wherein the compound iii) comprises one or more ester moieties.

Claim 51. (new) The methods of claim 48 wherein the compound iii) comprises one or more amide moieties.

Claim 52. (new) The method of claim 48 wherein the photoacid-generating compound is an iodonium compound.

Claim 53. (new) The method of claim 48 wherein the photoacid-generating compound is an aromatic sulfonium salt.

Claim 54. (new) The method of claim 48 wherein substrate areas bared of the photoresist layer upon development are selectively processed.

Claim 55. (new) The method of claim 48 wherein substrate areas bared of the photoresist upon development are chemically etched.

Claim 56. (new) The method of claim 48 wherein substrate areas bared of the photoresist layer upon development are plated.

Claim 57. (new) The method of claim 48 wherein the resin is a phenol-based polymer.